TEXAS INSTRUMENTS

CSD16323Q3

SLPS224C – AUGUST 2009 – REVISED NOVEMBER 2016

# CSD16323Q3 N-Channel NexFET™ Power MOSFET

1 Features

- Optimized for 5-V Gate Drive
- Ultra-Low Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Lead-Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 3.3-mm × 3.3-mm Plastic Package

2 Applications

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control or Synchronous FET Applications

3 Description

This 25-V, 3.8-mΩ, 3.3 × 3.3-mm SON NexFET™ power MOSFET has been designed to minimize losses in power conversion and optimized for 5-V gate drive applications.

Top View

P0095-01
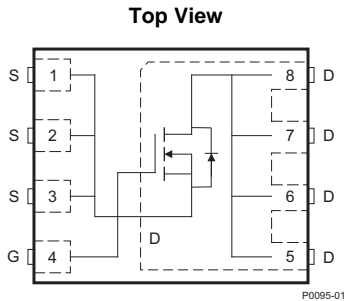
Product Summary

T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	25		V
Q_g	Gate Charge Total (4.5 V)	6.2		nC
Q_{gd}	Gate Charge Gate-to-Drain	1.1		nC
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = 3 V	5.4	mΩ
		V_{GS} = 4.5 V	4.4	
		V_{GS} = 8 V	3.8	
V_{th}	Threshold Voltage	1.1		V

Device Information[1]

DEVICE	MEDIA	QTY	PACKAGE	SHIP
CSD16323Q3	13-Inch Reel	2500	SON 3.30-mm × 3.30-mm Plastic Package	Tape and Reel
CSD16323Q3T	7-Inch Reel	250		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

T_A = 25°C (unless otherwise stated)		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	25	V
V_{GS}	Gate-to-Source Voltage	+10 / –8	V
I_D	Continuous Drain Current (Package Limit)	60	A
	Continuous Drain Current (Silicon Limited), T_C = 25°C	105	
	Continuous Drain Current[1]	20	
I_{DM}	Pulsed Drain Current[2]	240	A
P_D	Power Dissipation[1]	2.8	W
	Power Dissipation, T_C = 25°C	74	
T_J, T_{stg}	Operating Junction, Storage Temperature	–55 to 150	°C
E_{AS}	Avalanche Energy, Single Pulse I_D = 50 A, L = 0.1 mH, R_G = 25 Ω	125	mJ

(1) $R_{θJA}$ = 45°C/W on 1-in², 2-oz Cu pad on 0.06-in thick FR4 PCB.

(2) Max $R_{θJC}$ = 1.7°C/W, pulse duration ≤ 100 μs, duty cycle ≤ 1%.

$R_{DS(on)}$ vs V_{GS}

D007

Gate Charge

D004

Table of Contents

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (June 2011) to Revision C   **Page**

- Changed *Description* text 1
- Added silicon limited continuous drain current to *Absolute Maximum Ratings* table 1
- Changed Note 2 in *Absolute Maximum Ratings* table.. 1
- Changed values in the *Thermal Information* table to align with standards 3
- Changed Figure 1 to reflect a transient $R_{\theta JC}$ curve 4
- Changed Figure 10 to reflect measured data.. 5
- Added *Device and Documentation Support* section.. 7
- Changed *MECHANICAL DATA* section to *Mechanical, Packaging, and Orderable Information* section 8

Changes from Revision A (April 2010) to Revision B   **Page**

- Replaced the THERMAL CHARACTERISTICS table with the new Thermal Information Table... 4
- Replaced Figure 10 - Maximum Safe Operating Area 5

Changes from Original (August 2009) to Revision A   **Page**

- Changed $R_{DS(on)}$ - V_{GS} = 3 V, I_D = 24 A MAX value From: 6.5 To: 7.2 3

Product Folder Links: *CSD16323Q3*

5 Specifications

5.1 Electrical Characteristics

T_A = 25°C (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-source voltage	V_{GS} = 0 V, I_D = 250 µA	25			V
I_{DSS}	Drain-to-source leakage current	V_{GS} = 0 V, V_{DS} = 20 V			1	µA
I_{GSS}	Gate-to-source leakage current	V_{DS} = 0 V, V_{GS} = +10/-8 V			100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	0.9	1.1	1.4	V
$R_{DS(on)}$	Drain-to-source on-resistance	V_{GS} = 3 V, I_D = 24 A		5.4	7.2	mΩ
		V_{GS} = 4.5 V, I_D = 24 A		4.4	5.5	
		V_{GS} = 8 V, I_D = 24 A		3.8	4.5	
g_{fs}	Transconductance	V_{DS} = 12.5 V, I_D = 24 A		108		S
DYNAMIC CHARACTERISTICS						
C_{ISS}	Input capacitance	V_{GS} = 0 V, V_{DS} = 12.5 V, f = 1 MHz		1020	1300	pF
C_{OSS}	Output capacitance			740	960	pF
C_{RSS}	Reverse transfer capacitance			50	65	pF
R_g	Series gate resistance			1.4	2.8	Ω
Q_g	Gate charge total (4.5 V)	V_{DS} = 12.5 V, I_D = 24 A		6.2	8.4	nC
Q_{gd}	Gate charge gate-to-drain			1.1		nC
Q_{gs}	Gate charge gate-to-source			1.8		nC
Qg(th)	Gate charge at Vth			1		nC
Q_{OSS}	Output charge	V_{DS} = 12.5 V, V_{GS} = 0 V		14		nC
$t_{d(on)}$	Turnon delay time	V_{DS} = 12.5 V, V_{GS} = 4.5 V, I_D = 24 A R_G = 2 Ω		5.3		ns
t_r	Rise time			15		ns
$t_{d(off)}$	Turnoff delay time			13		ns
t_f	Fall time			6.3		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode forward voltage	I_S = 24 A, V_{GS} = 0 V		0.85	1	V
Q_{rr}	Reverse recovery charge	V_{DD} = 12.5 V, I_F = 24 A, di/dt = 300 A/µs		21		nC
t_{rr}	Reverse recovery time	V_{DD} = 12.5 V, I_F = 24 A, di/dt = 300 A/µs		16		ns

5.2 Thermal Information

T_A = 25°C (unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance[1]			1.7	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance[1][2]			55	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-in^2 (6.45-cm^2), 2-oz (0.071-mm) thick Cu pad on a 1.5-in × 1.5-in (3.81-cm × 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
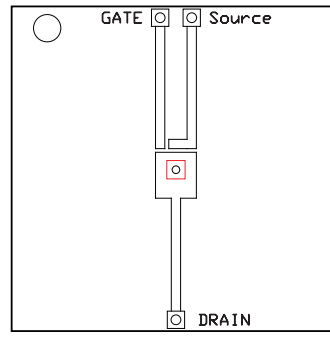(2)   Device mounted on FR4 material with 1-in^2 (6.45-cm^2), 2-oz (0.071-mm) thick Cu.

Product Folder Links: *CSD16323Q3*
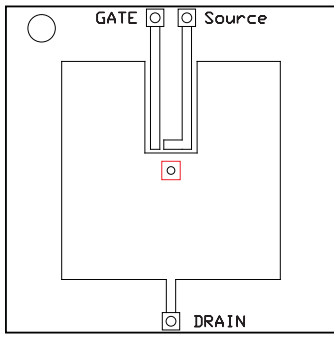
Max $R_{\theta JA}$ = 55°C/W when mounted on 1 in^2 of 2-oz Cu.

Max $R_{\theta JA}$ = 160°C/W when mounted on minimum pad area of 2-oz Cu.

5.3 Typical MOSFET Characteristics

T_A = 25°C (unless otherwise stated)

Figure 1. Transient Thermal Impedance
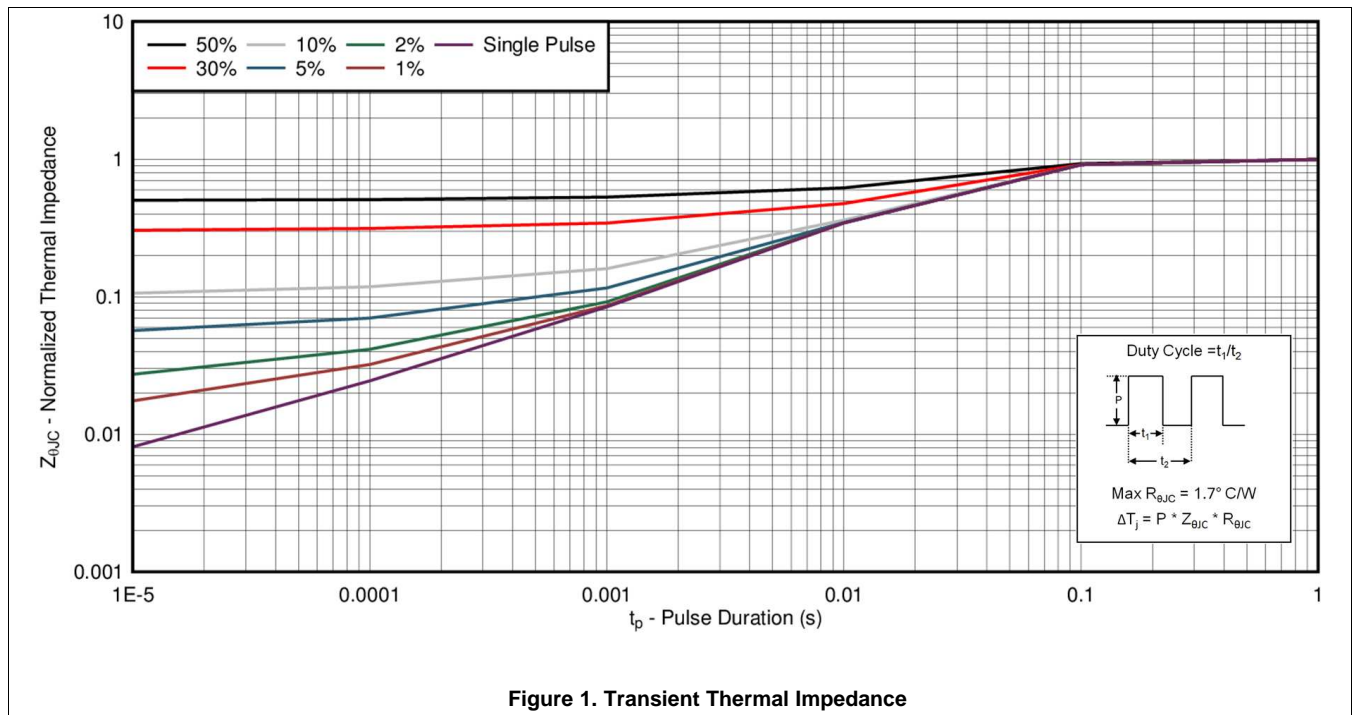
Product Folder Links: *CSD16323Q3*

Typical MOSFET Characteristics (continued)

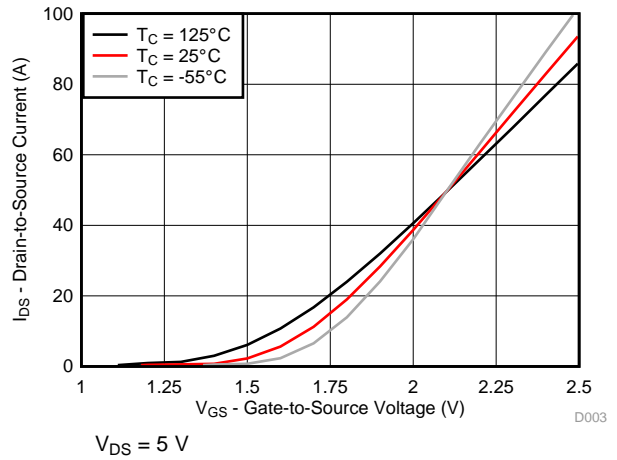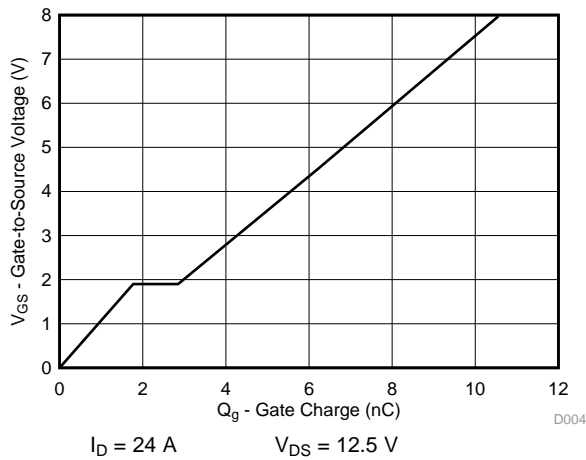T_A = 25°C (unless otherwise stated)
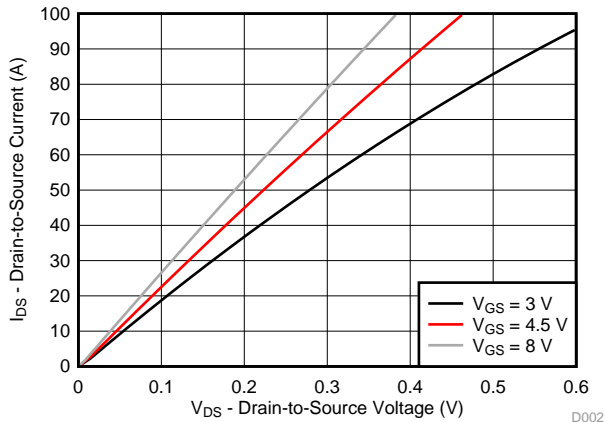
Figure 2. Saturation Characteristics

V_{GS} = 3 V
V_{GS} = 4.5 V
V_{GS} = 8 V

Figure 3. Transfer Characteristics

T_C = 125°C
T_C = 25°C
T_C = -55°C

V_{DS} = 5 V

I_D = 24 A V_{DS} = 12.5 V

Figure 4. Gate Charge

$C_{iss} = C_{gd} + C_{gs}$
$C_{oss} = C_{ds} + C_{gd}$
$C_{rss} = C_{gd}$

f = 1 MHz V_{GS} = 0 V
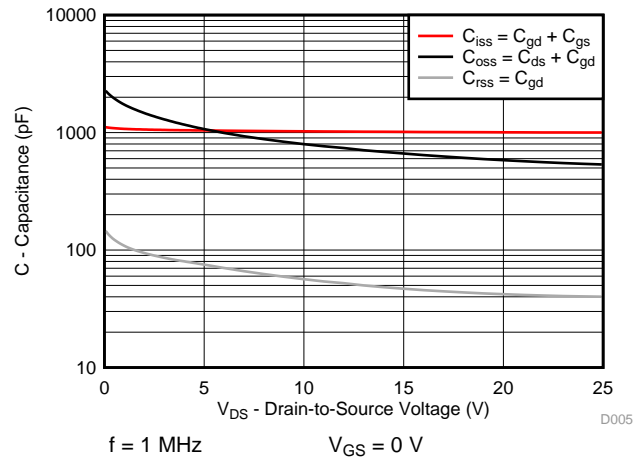
Figure 5. Capacitance

I_D = 250 µA
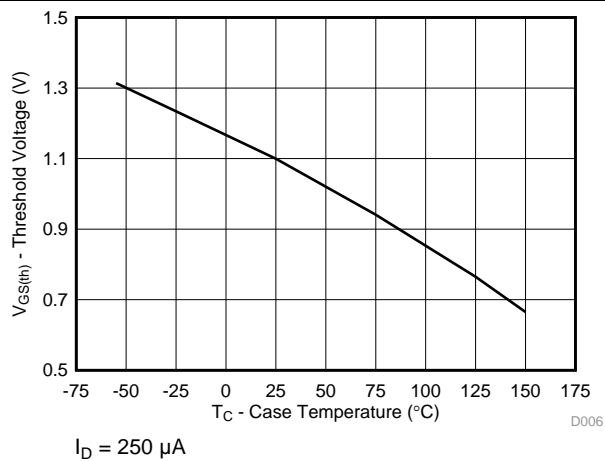
Figure 6. Threshold Voltage vs Temperature

T_C = 25°C, I_D = 24 A
T_C = 125°C, I_D = 24 A

I_D = 24 A
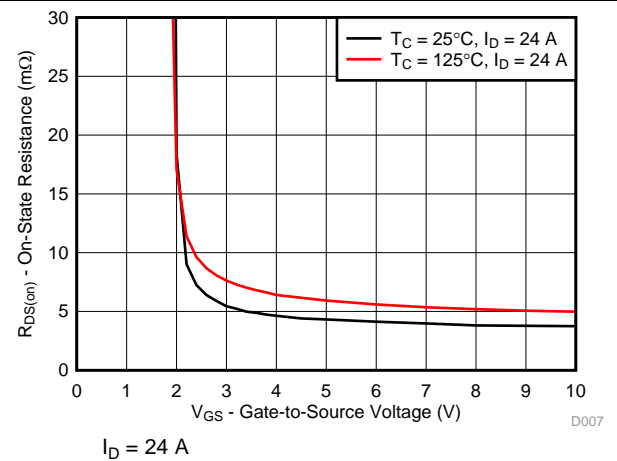
Figure 7. On Resistance vs Gate Voltage

Product Folder Links: *CSD16323Q3*

Typical MOSFET Characteristics (continued)

T_A = 25°C (unless otherwise stated)

I_D = 24 A V_{GS} = 4.5 V
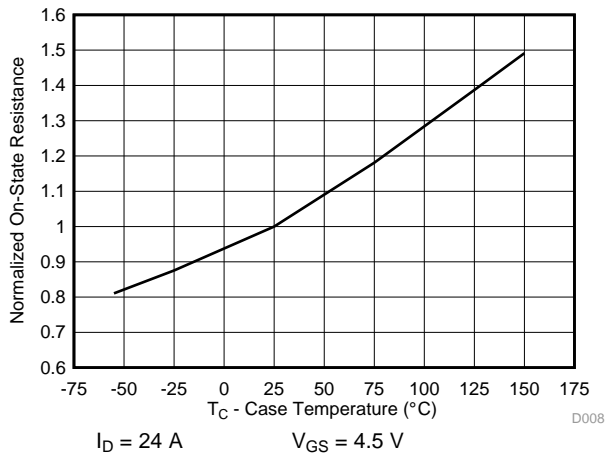
Figure 8. Normalized On Resistance vs Temperature
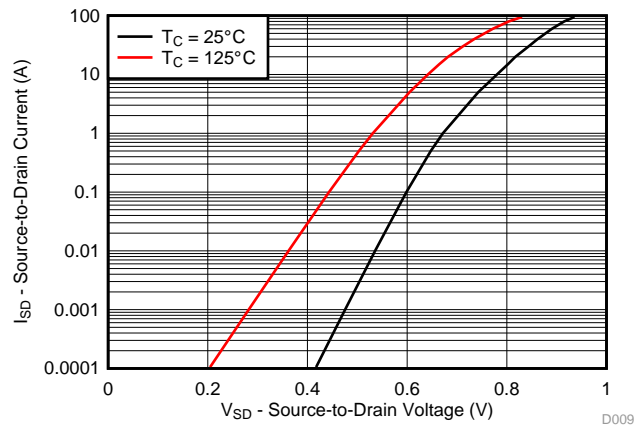
Figure 9. Typical Diode Forward Voltage

Single pulse, max $R_{\theta JC}$ = 1.7°C/W
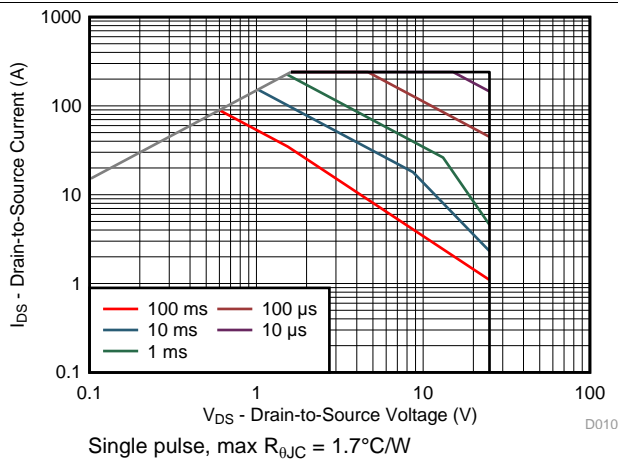
Figure 10. Maximum Safe Operating Area
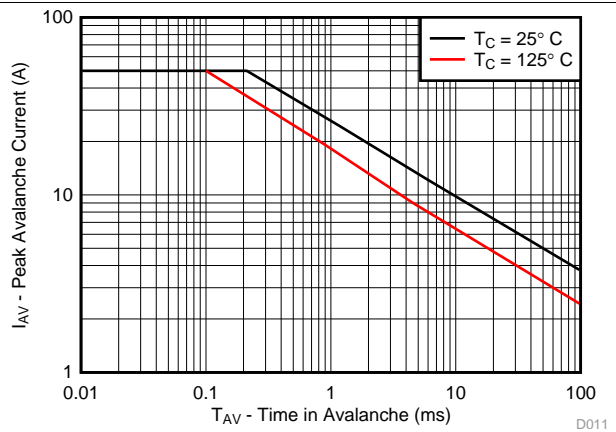
Figure 11. Single Pulse Unclamped Inductive Switching
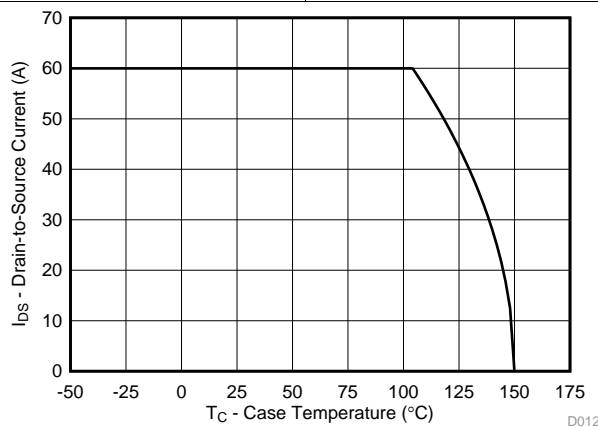
Figure 12. Maximum Drain Current vs Temperature

Product Folder Links: *CSD16323Q3*

6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.3 Trademarks

NexFET, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

6.4 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q3 Package Dimensions

Top View

Side View

Bottom View

Front View
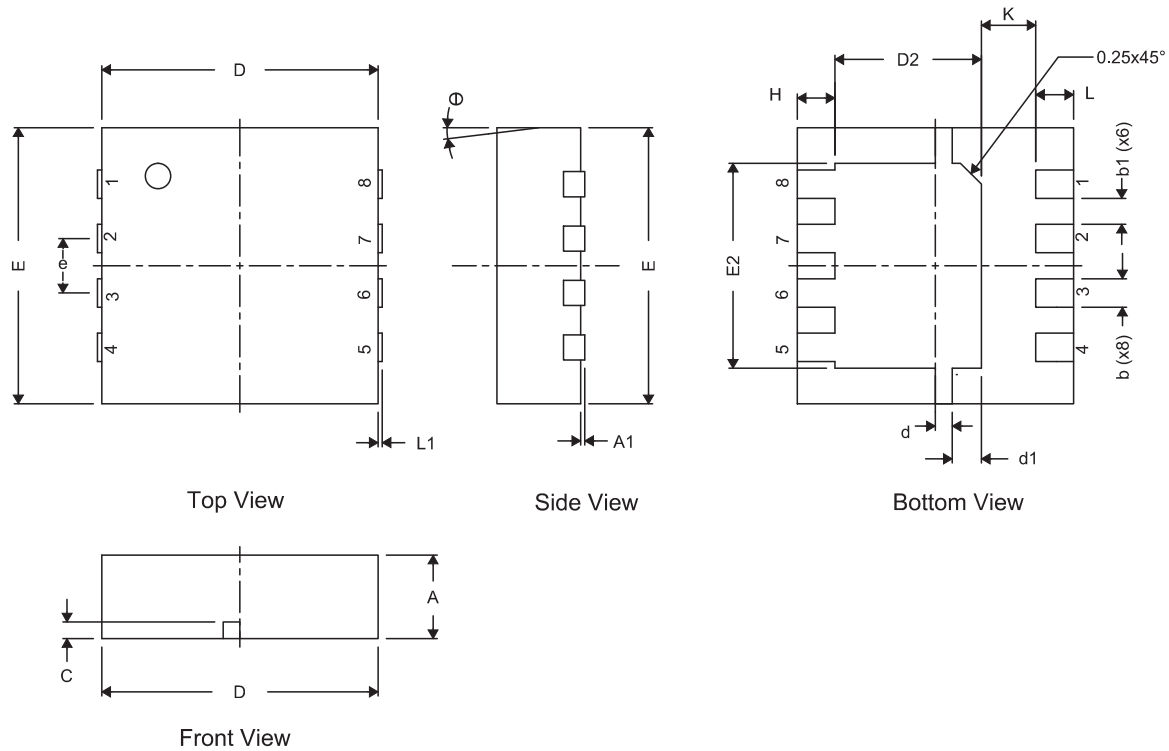
DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.950	1.000	1.100	0.037	0.039	0.043
A1	0.000	0.000	0.050	0.000	0.000	0.002
b	0.280	0.340	0.400	0.011	0.013	0.016
b1		0.310 NOM			0.012 NOM	
c	0.150	0.200	0.250	0.006	0.008	0.010
D	3.200	3.300	3.400	0.126	0.130	0.134
D2	1.650	1.750	1.800	0.065	0.069	0.071
d	0.150	0.200	0.250	0.006	0.008	0.010
d1	0.300	0.350	0.400	0.012	0.014	0.016
E	3.200	3.300	3.400	0.126	0.130	0.134
E2	2.350	2.450	2.550	0.093	0.096	0.100
e		0.650 TYP			0.026 TYP	
H	0.35	0.450	0.550	0.014	0.018	0.022
K		0.650 TYP			0.026 TYP	
L	0.35	0.450	0.550	0.014	0.018	0.022
L1	0	—	0	0	—	0
θ	0	—	0	0	—	0

Product Folder Links: *CSD16323Q3*

7.2 Recommended PCB Pattern
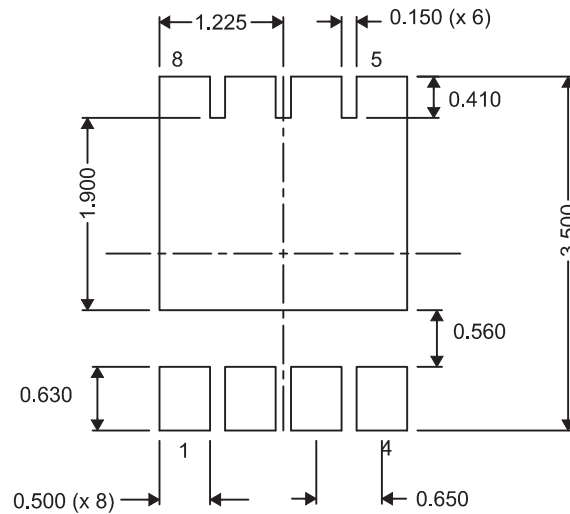
For recommended circuit layout for PCB designs, see *Reducing Ringing Through PCB Layout Techniques* (SLPA005).

7.3 Recommended Stencil Opening

All dimensions are in mm, unless otherwise specified.

Product Folder Links: *CSD16323Q3*
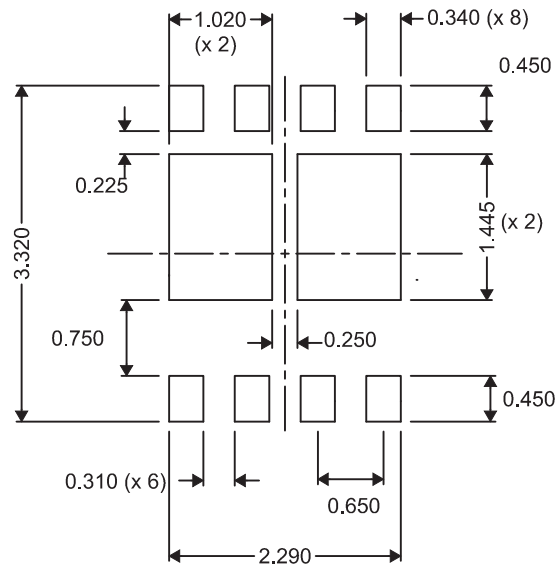
7.4 Q3 Tape and Reel Information

M0144-01

Notes:

1. 10 sprocket hole pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm.
3. Material: black static dissipative polystyrene.
4. All dimensions are in mm (unless otherwise specified).
5. Thickness: 0.30 ±0.05 mm.
6. MSL1 260°C (IR and Convection) PbF-Reflow Compatible.

Product Folder Links: *CSD16323Q3*

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD16323Q3	ACTIVE	VSON-CLIP	DQG	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD16323	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

IMPORTANT NOTICE

Products		Applications	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	**TI E2E Community**	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconnectivity		